

Hitachi Single-Chip Microcomputer

H8S/2148 Series

H8S/2144 Series

Hardware Manual
Supplementary Edition

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Section 25 Electrical Characteristics

25.1 Absolute Maximum Ratings

Table 25.1 lists the absolute maximum ratings. The H8S/2144 Series does not support the VCCB pin function, so V_{CCB} should be read as V_{CC} in the tables for this series.

Table 25.1 Absolute Maximum Ratings

– Preliminary –

Item	Symbol	Value	Unit
Power supply voltage	V_{CC}	–0.3 to +7.0	V
Input voltage (except ports 6, 7, and A)	V_{in}	–0.3 to $V_{CC} + 0.3$	V
Input voltage (CIN input not selected for port 6)	V_{in}	–0.3 to $V_{CC} + 0.3$	V
Input voltage (CIN input not selected for port A)	V_{in}	–0.3 to $V_{CCB} + 0.3$	V
Input voltage (CIN input selected for port 6)	V_{in}	–0.3 V to lower of voltages $V_{CC} + 0.3$ and $AV_{CC} + 0.3$	V
Input voltage (CIN input selected for port A)	V_{in}	–0.3 V to lower of voltages $V_{CCB} + 0.3$ and $AV_{CC} + 0.3$	V
Input voltage (port 7)	V_{in}	–0.3 to $AV_{CC} + 0.3$	V
Reference supply voltage	AV_{ref}	–0.3 to $AV_{CC} + 0.3$	V
Analog power supply voltage	AV_{CC}	–0.3 to +7.0	V
Analog input voltage	V_{AN}	–0.3 to $AV_{CC} + 0.3$	V
Operating temperature	T_{opr}	Regular specifications: –20 to +75	°C
		Wide-range specifications: –40 to +85	°C
Storage temperature	T_{stg}	–55 to +125	°C

Caution: Permanent damage to the chip may result if absolute maximum ratings are exceeded.

* A range of 0 to +75°C must be observed for flash memory programming/erasing in the F-ZTAT version.

25.2 DC Characteristics

Table 25.2 lists the DC characteristics. Permitted output current values and bus drive characteristics are shown in tables 25.3 and 25.4, respectively. The H8S/2144 Series does not support the VCCB pin function, so V_{CCB} should be read as V_{CC} in the tables for this series.

Table 25.2 DC Characteristics

– Preliminary –

Conditions: V_{CC} = 5.0 V ± 10%, V_{CCB} = 5.0 V ± 10%, AV_{CC}*¹ = 5.0 V ± 10%,
AV_{ref}*¹ = 4.5 V to AV_{CC}, V_{SS} = AV_{SS}*¹ = 0 V, T_a = -20 to +75°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Schmitt trigger input voltage	P67 to P60* ^{2, *6} , (1)* ⁸ KIN15 to KIN8* ⁷	V _T ⁻	1.0	—	—	V	
	IRQ2 to IRQ0* ³ , IRQ5 to IRQ3	V _T ⁺	—	—	V _{CC} × 0.7 V _{CCB} × 0.7	V	
		V _T ⁺ - V _T ⁻	0.4	—	—	V	
Input high voltage	RES, STBY, NMI, MD1, MD0	(2) V _{IH}	V _{CC} - 0.7	—	V _{CC} + 0.3	V	
	EXTAL		V _{CC} × 0.7	—	V _{CC} + 0.3	V	
	PA7 to PA0* ⁷		V _{CCB} × 0.7	—	V _{CCB} + 0.3	V	
	Port 7		2.0	—	AV _{CC} + 0.3	V	
	Input pins except (1) and (2) above* ⁶		2.0	—	V _{CC} + 0.3	V	
Input low voltage	RES, STBY, MD1, MD0	(3) V _{IL}	-0.3	—	0.5	V	
	PA7 to PA0		-0.3	—	1.0	V	
	NMI, EXTAL, input pins except (1) and (3) above		-0.3	—	0.8	V	
Output high voltage	All output pins (except P97, and P52)* ^{5, *8}	V _{OH}	V _{CC} - 0.5 V _{CCB} - 0.5	—	—	V	I _{OH} = -200 μA
			3.5	—	—	V	I _{OH} = -1 mA
	P97, P52* ⁴		2.5	—	—	V	I _{OH} = -1 mA

Table 25.2 DC Characteristics (cont)

– Preliminary –

Conditions: $V_{CC} = 5.0\text{ V} \pm 10\%$, $V_{CCB} = 5.0\text{ V} \pm 10\%$, $AV_{CC}^{*1} = 5.0\text{ V} \pm 10\%$,
 $AV_{ref}^{*1} = 4.5\text{ V}$ to AV_{CC} , $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications), $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Output low voltage	All output pins (except $\overline{\text{RESO}}$)* ⁵	V_{OL}	—	—	0.4	V	$I_{OL} = 1.6\text{ mA}$
	Ports 1 to 3		—	—	1.0	V	$I_{OL} = 10\text{ mA}$
	$\overline{\text{RESO}}$		—	—	0.4	V	$I_{OL} = 2.6\text{ mA}$
Input leakage current	$\overline{\text{RES}}$	$ I_{in} $	—	—	10.0	μA	$V_{in} = 0.5$ to $V_{CC} - 0.5\text{ V}$
	$\overline{\text{STBY}}$, NMI, MD1, MD0		—	—	1.0	μA	
	Port 7		—	—	1.0	μA	$V_{in} = 0.5$ to $AV_{CC} - 0.5\text{ V}$
Three-state leakage current (off state)	Ports 1 to 6 Ports 8, 9, A* ⁸ , B	$ I_{TSI} $	—	—	1.0	μA	$V_{in} = 0.5$ to $V_{CC} - 0.5\text{ V}$, $V_{in} = 0.5$ to $V_{CCB} - 0.5\text{ V}$
Input pull-up MOS current	Ports 1 to 3	$-I_P$	50	—	300	μA	$V_{in} = 0\text{ V}$
	Ports 6, A* ⁸ , B		60	—	500	μA	
Input capacitance	$\overline{\text{RES}}$ (4)	C_{in}	—	—	80	pF	$V_{in} = 0\text{ V}$ $f = 1\text{ MHz}$ $T_a = 25^\circ\text{C}$
	NMI		—	—	50	pF	
	P52, P97, P42, P86 PA7 to PA2		—	—	20	pF	
	Input pins except (4) above		—	—	15	pF	

Table 25.2 DC Characteristics (cont)
– Preliminary –

Conditions: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{CCB} = 5.0 \text{ V} \pm 10\%$, $AV_{CC}^{*1} = 5.0 \text{ V} \pm 10\%$,
 $AV_{ref}^{*1} = 4.5 \text{ V}$ to AV_{CC} , $V_{SS} = AV_{SS}^{*1} = 0 \text{ V}$, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications), $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Current dissipation* ⁹	Normal operation	I_{CC}	—	75	100	mA	f = 20 MHz, H8S/2144 Series
			—	85	120	mA	f = 20 MHz, H8S/2148 Series
	Sleep mode		—	60	85	mA	f = 20 MHz, H8S/2144 Series
			—	70	100	mA	f = 20 MHz, H8S/2148 Series
	Standby mode* ¹⁰		—	0.01	5.0	μA	$T_a \leq 50^\circ\text{C}$
			—	—	20.0	μA	$50^\circ\text{C} < T_a$
Analog power supply current	During A/D, D/A conversion	AI_{CC}	—	1.2	2.0	mA	
	Idle		—	0.01	5.0	μA	$AV_{CC} = 2.0 \text{ V}$ to 5.5 V
Reference power supply current	During A/D conversion	AI_{ref}	—	0.5	1.0	mA	
	During A/D, D/A conversion		—	2.0	5.0	mA	
	Idle		—	0.01	5.0	μA	$AV_{ref} = 2.0 \text{ V}$ to AV_{CC}
Analog power supply voltage* ¹		AV_{CC}	4.5	—	5.5	V	Operating
			2.0	—	5.5	V	Idle/not used
RAM standby voltage		V_{RAM}	2.0	—	—	V	

Notes: 1. Do not leave the AV_{CC} , AV_{ref}^{*1} and AV_{SS} pins open even if the A/D converter and D/A converter are not used.

Even if the A/D converter and D/A converter are not used, apply a value in the range 2.0 V to 5.5 V to AV_{CC} and AV_{ref} pins by connection to the power supply (V_{CC}), or some other method. Ensure that $AV_{ref} \leq AV_{CC}$.

- P67 to P60 include supporting module inputs multiplexed on those pins.
- $\overline{\text{IRQ2}}$ includes the $\overline{\text{ADTRG}}$ signal multiplexed on that pin.

4. P52/SCK0/SCL0 and P97/SDA0 are NMOS push-pull outputs.
An external pull-up resistor is necessary to provide high-level output from SCL0 and SDA0 (ICE = 1).
P52/SCK0 and P97 (ICE = 0) high levels are driven by NMOS.
5. When IICS = 0, ICE = 0, and KBIOE = 0. Low-level output when the bus drive function is selected is determined separately.
6. The upper limit of the port 6 applied voltage is $V_{CC} + 0.3\text{ V}$ when CIN input is not selected, and the lower of $V_{CC} + 0.3\text{ V}$ and $AV_{CC} + 0.3\text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
7. The upper limit of the port A applied voltage is $V_{CCB} + 0.3\text{ V}$ when CIN input is not selected, and the lower of $V_{CCB} + 0.3\text{ V}$ and $AV_{CC} + 0.3\text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
8. The port A characteristics depend on V_{CCB} , and the other pins characteristics depend on V_{CC} .
9. Current dissipation values are for $V_{IH\text{ min}} = V_{CC} - 0.5\text{ V}$, $V_{CCB} \times 0.9$, and $V_{IL\text{ max}} = 0.5\text{ V}$ with all output pins unloaded and the on-chip pull-up MOSs in the off state.
10. The values are for $V_{RAM} \leq V_{CC} < 4.5\text{V}$, $V_{IH\text{ min}} = V_{CC} \times 0.9$, $V_{CCB} \times 0.9$, and $V_{IL\text{ max}} = 0.3\text{ V}$.

Table 25.2 DC Characteristics (cont)
– Preliminary –

Conditions: $V_{CC} = 4.0\text{ V to }5.5\text{ V}^{*9}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 4.0\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 4.0\text{ V to }AV_{CC}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}^{*9}$ (regular specifications), $T_a = -40\text{ to }+85^\circ\text{C}^{*9}$ (wide-range specifications)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Schmitt trigger input voltage	P67 to P60 ^{*2, *6} , (1) ^{*8} KIN15 to KIN8 ^{*7} , IRQ2 to IRQ0 ^{*3} , IRQ5 to IRQ3	V_T^-	1.0	—	—	V	$V_{CC} =$ 4.5 V to 5.5 V, $V_{CCB} =$ 4.5 V to 5.5 V
		V_T^+	—	—	$V_{CC} \times 0.7$ $V_{CCB} \times 0.7$	V	
		$V_T^+ - V_T^-$	0.4	—	—	V	
		V_T^-	0.8	—	—	V	$V_{CC} =$ 4.0 V to 4.5 V, $V_{CCB} =$ 4.0 V to 4.5 V
		V_T^+	—	—	$V_{CC} \times 0.7$ $V_{CCB} \times 0.7$	V	
		$V_T^+ - V_T^-$	0.3	—	—	V	
Input high voltage	\overline{RES} , \overline{STBY} , (2) NMI, MD1, MD0	V_{IH}	$V_{CC} - 0.7$	—	$V_{CC} + 0.3$	V	
	EXTAL		$V_{CC} \times 0.7$	—	$V_{CC} + 0.3$	V	
	PA7 to PA0 ^{*7}		$V_{CCB} \times 0.7$	—	$V_{CCB} + 0.3$	V	
	Port 7		2.0	—	$AV_{CC} + 0.3$	V	
	Input pins except (1) and (2) above ^{*6}		2.0	—	$V_{CC} + 0.3$	V	
Input low voltage	\overline{RES} , \overline{STBY} , (3) MD1, MD0	V_{IL}	-0.3	—	0.5	V	
	PA7 to PA0		-0.3	—	1.0	V	$V_{CCB} =$ 4.5 V to 5.5 V
			-0.3	—	0.8	V	$V_{CCB} =$ 4.0 V to 4.5 V
	NMI, EXTAL, input pins except (1) and (3) above		-0.3	—	0.8	V	

Table 25.2 DC Characteristics (cont)

– Preliminary –

Conditions: $V_{CC} = 4.0\text{ V to }5.5\text{ V}^{*9}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 4.0\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 4.0\text{ V to }AV_{CC}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}^{*9}$ (regular specifications), $T_a = -40\text{ to }+85^\circ\text{C}^{*9}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions	
Output high voltage	All output pins (except P97, and P52) ^{*5, *8}	V_{OH}	$V_{CC} - 0.5$	—	—	V	$I_{OH} = -200\ \mu\text{A}$	
			$V_{CCB} - 0.5$					
			3.5	—	—	V	$I_{OH} = -1\text{ mA}$, $V_{CC} = 4.5\text{ V to }5.5\text{ V}$, $V_{CCB} = 4.5\text{ V to }5.5\text{ V}$	
			3.0	—	—	V	$I_{OH} = -1\text{ mA}$, $V_{CC} = 4.0\text{ V to }4.5\text{ V}$, $V_{CCB} = 4.0\text{ V to }4.5\text{ V}$	
	P97, P52 ^{*4}		2.0	—	—	V	$I_{OH} = -1\text{ mA}$	
Output low voltage	All output pins (except $\overline{\text{RESO}}$) ^{*5}	V_{OL}	—	—	0.4	V	$I_{OL} = 1.6\text{ mA}$	
			Ports 1 to 3	—	—	1.0	V	$I_{OL} = 10\text{ mA}$
			$\overline{\text{RESO}}$	—	—	0.4	V	$I_{OL} = 2.6\text{ mA}$
Input leakage current	RES	$ I_{in} $	—	—	10.0	μA	$V_{in} = 0.5\text{ to }V_{CC} - 0.5\text{ V}$	
	$\overline{\text{STBY}}$, NMI, MD1, MD0		—	—	1.0	μA		
	Port 7		—	—	1.0	μA	$V_{in} = 0.5\text{ to }AV_{CC} - 0.5\text{ V}$	
Three-state leakage current (off state)	Ports 1 to 6 Ports 8, 9, A ^{*8} , B	$ I_{TSI} $	—	—	1.0	μA	$V_{in} = 0.5\text{ to }V_{CC} - 0.5\text{ V}$, $V_{in} = 0.5\text{ to }V_{CCB} - 0.5\text{ V}$	

Table 25.2 DC Characteristics (cont)
– Preliminary –

Conditions: $V_{CC} = 4.0\text{ V to }5.5\text{ V}^{*9}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 4.0\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 4.0\text{ V to }AV_{CC}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}^{*9}$ (regular specifications), $T_a = -40\text{ to }+85^\circ\text{C}^{*9}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Input pull-up current	Ports 1 to 3	$-I_P$	50	—	300	μA	$V_{in} = 0\text{ V}$, $V_{CC} = 4.5\text{ V to }5.5\text{ V}$, $V_{CCB} = 4.5\text{ V to }5.5\text{ V}$
	Ports 6, A* ⁸ , B		60	—	500	μA	
	Ports 1 to 3		30	—	200	μA	
	Ports 6, A* ⁸ , B		40	—	400	μA	
Input capacitance	$\overline{\text{RES}}$	(4) C_{in}	—	—	80	pF	$V_{in} = 0\text{ V}$, $f = 1\text{ MHz}$, $T_a = 25^\circ\text{C}$
	NMI		—	—	50	pF	
	P52, P97, P42, P86, PA7 to PA2		—	—	20	pF	
	Input pins except (4) above		—	—	15	pF	
Current dissipation* ¹⁰	Normal operation	I_{CC}	—	65	85	mA	f = 16 MHz, H8S/2144 Series
			—	70	100	mA	f = 16 MHz, H8S/2148 Series
	Sleep mode		—	50	70	mA	f = 16 MHz, H8S/2144 Series
			—	60	85	mA	f = 16 MHz, H8S/2148 Series
	Standby mode* ¹¹		—	0.01	5.0	μA	$T_a \leq 50^\circ\text{C}$
			—	—	20.0	μA	$50^\circ\text{C} < T_a$

Conditions: $V_{CC} = 4.0\text{ V to }5.5\text{ V}^{*9}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 4.0\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 4.0\text{ V to }AV_{CC}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}^{*9}$ (regular specifications), $T_a = -40\text{ to }+85^\circ\text{C}^{*9}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Analog power supply current	During A/D, D/A conversion	AI_{CC}	—	1.2	2.0	mA	
	Idle		—	0.01	5.0	μA	$AV_{CC} = 2.0\text{ V to }5.5\text{ V}$
Reference power supply current	During A/D conversion	AI_{ref}	—	0.5	1.0	mA	
	During A/D, D/A conversion		—	2.0	5.0	mA	
	Idle		—	0.01	5.0	μA	$AV_{ref} = 2.0\text{ V to }AV_{CC}$
Analog power supply voltage ^{*1}		AV_{CC}	4.0	—	5.5	V	Operating
			2.0	—	5.5	V	Idle/not used
RAM standby voltage		V_{RAM}	2.0	—	—	V	

- Notes: 1. Do not leave the AV_{CC} , AV_{ref} , and AV_{SS} pins open even if the A/D converter and D/A converter are not used.
 Even if the A/D converter and D/A converter are not used, apply a value in the range 2.0 V to 5.5 V to AV_{CC} and AV_{ref} pins by connection to the power supply (V_{CC}), or some other method. Ensure that $AV_{ref} \leq AV_{CC}$.
2. P67 to P60 include supporting module inputs multiplexed on those pins.
3. $\overline{IRQ2}$ includes the \overline{ADTRG} signal multiplexed on that pin.
4. P52/SCK0/SCL0 and P97/SDA0 are NMOS push-pull outputs.
 An external pull-up resistor is necessary to provide high-level output from SCL0 and SDA0 (ICE = 1).
 P52/SCK0 and P97 (ICE = 0) high levels are driven by NMOS.
5. When IICS = 0, ICE = 0, and KBIOE = 0. Low-level output when the bus drive function is selected is determined separately.
6. The upper limit of the port 6 applied voltage is $V_{CC} + 0.3\text{ V}$ when CIN input is not selected, and the lower of $V_{CC} + 0.3\text{ V}$ and $AV_{CC} + 0.3\text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
7. The upper limit of the port A applied voltage is $V_{CCB} + 0.3\text{ V}$ when CIN input is not selected, and the lower of $V_{CCB} + 0.3\text{ V}$ and $AV_{CC} + 0.3\text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
8. The port A characteristics depend on V_{CCB} , and the other pins characteristics depend on V_{CC} .
9. Ranges of $V_{CC} = 4.5\text{ to }5.5\text{ V}$ and $T_a = 0\text{ to }+75^\circ\text{C}$ must be observed for flash memory programming/erasing.

10. Current dissipation values are for $V_{IH} \text{ min} = V_{CC} - 0.5 \text{ V}$, $V_{CCB} - 0.5 \text{ V}$, and $V_{IL} \text{ max} = 0.5 \text{ V}$ with all output pins unloaded and the on-chip pull-up MOSs in the off state.
11. The values are for $V_{RAM} \leq V_{CC} < 4.5 \text{ V}$, $V_{IH} \text{ min} = V_{CC} \times 0.9$, $V_{CCB} \times 0.9$, and $V_{IL} \text{ max} = 0.3 \text{ V}$.

Table 25.2 DC Characteristics (cont)

– Preliminary –

Conditions*⁹: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 2.7\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Schmitt trigger input voltage	P67 to P60* ^{2, *6} , (1)* ⁸ KIN15 to KIN8* ⁷ , IRQ2 to IRQ0* ³ , IRQ5 to IRQ3	V_T^-	$V_{CC} \times 0.2$	—	—	V	
		V_T^+	—	—	$V_{CC} \times 0.7$ $V_{CCB} \times 0.7$	V	
		$V_T^+ - V_T^-$	$V_{CC} \times 0.05$ $V_{CCB} \times 0.05$	—	—	V	
Input high voltage	\overline{RES} , \overline{STBY} , NMI, MD1, MD0	(2) V_{IH}	$V_{CC} \times 0.9$	—	$V_{CC} + 0.3$	V	
	EXTAL		$V_{CC} \times 0.7$	—	$V_{CC} + 0.3$	V	
	PA7 to PA0* ⁷		$V_{CCB} \times 0.7$	—	$V_{CCB} + 0.3$	V	
	Port 7		$V_{CC} \times 0.7$	—	$AV_{CC} + 0.3$	V	
	Input pins except (1) and (2) above* ⁶		$V_{CC} \times 0.7$	—	$V_{CC} + 0.3$	V	
Input low voltage	\overline{RES} , \overline{STBY} , MD1, MD0	(3) V_{IL}	-0.3	—	$V_{CC} \times 0.1$	V	
	PA7 to PA0		-0.3	—	$V_{CCB} \times 0.2$	V	
					0.8	V	
						$V_{CCB} = 2.7\text{ V to }4.0\text{ V}$ $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$	
	NMI, EXTAL, input pins except (1) and (3) above		-0.3	—	$V_{CC} \times 0.2$	V	
					0.8	V	
						$V_{CC} = 2.7\text{ V to }4.0\text{ V}$ $V_{CC} = 4.0\text{ V to }5.5\text{ V}$	
Output high voltage	All output pins (except P97, and P52)* ^{5, *8}	V_{OH}	$V_{CC} - 0.5$	—	—	V	$I_{OH} = -200\ \mu\text{A}$
			$V_{CCB} - 0.5$				
		$V_{CC} - 1.0$ $V_{CCB} - 1.0$	—	—	V	$I_{OH} = -1\text{ mA}$ ($V_{CC} = 2.7\text{ V to }4.0\text{ V}$, $V_{CCB} = 2.7\text{ V to }4.0\text{ V}$)	
	P97, P52* ⁴		1.0	—	—	V	$I_{OH} = -1\text{ mA}$

Table 25.2 DC Characteristics (cont)
– Preliminary –

Conditions*⁹: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 2.7\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Output low voltage	All output pins (except RESO)* ⁵	V_{OL}	—	—	0.4	V	$I_{OL} = 0.8\text{ mA}$
	Ports 1 to 3		—	—	1.0	V	$I_{OL} = 5\text{ mA}$ ($V_{CC} \leq 4.0\text{ V}$), $I_{OL} = 10\text{ mA}$ ($4.0\text{ V} \leq V_{CC} \leq 5.5\text{ V}$)
	RESO		—	—	0.4	V	$I_{OL} = 0.8\text{ mA}$
Input leakage current	RES	$ I_{in} $	—	—	10.0	μA	$V_{in} = 0.5\text{ to }V_{CC} - 0.5\text{ V}$
	STBY, NMI, MD1, MD0		—	—	1.0	μA	
	Port 7		—	—	1.0	μA	$V_{in} = 0.5\text{ to }AV_{CC} - 0.5\text{ V}$
Three-state leakage current (off state)	Ports 1 to 6 Ports 8, 9, A* ⁸ , B	$ I_{TSL} $	—	—	1.0	μA	$V_{in} = 0.5\text{ to }V_{CC} - 0.5\text{ V}$, $V_{in} = 0.5\text{ to }V_{CCB} - 0.5\text{ V}$
Input pull-up MOS current	Ports 1 to 3	$-I_p$	10	—	150	μA	$V_{in} = 0\text{ V}$, $V_{CC} = 2.7\text{ V to }3.6\text{ V}$,
	Ports 6, A* ⁸ , B		30	—	250	μA	$V_{CCB} = 2.7\text{ V to }3.6\text{ V}$
Input capacitance	RES (4)	C_{in}	—	—	80	pF	$V_{in} = 0\text{ V}$, $f = 1\text{ MHz}$,
	NMI		—	—	50	pF	$T_a = 25^\circ\text{C}$
	P52, P97, P42, P86, PA7 to PA2		—	—	20	pF	
	Input pins except (4) above		—	—	15	pF	

Table 25.2 DC Characteristics (cont)

– Preliminary –

Conditions*⁹: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $AV_{CC}^{*1} = 2.7\text{ V to }5.5\text{ V}$,
 $AV_{ref}^{*1} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = AV_{SS}^{*1} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Current dis- sipation* ¹⁰	Normal operation	I_{CC}	—	45	60	mA	f = 10 MHz, H8S/2144 Series
			—	50	70		f = 10 MHz, H8S/2148 Series
	Sleep mode		—	35	50	mA	f = 10 MHz, H8S/2144 Series
			—	40	60		f = 10 MHz, H8S/2148 Series
	Standby mode* ¹¹		—	0.01	5.0	μA	$T_a \leq 50^\circ\text{C}$
			—	—	20.0		$50^\circ\text{C} < T_a$
Analog power supply current	During A/D, D/A conversion	AI_{CC}	—	1.2	2.0	mA	
	Idle		—	0.01	5.0		μA
Reference power supply current	During A/D conversion	AI_{ref}	—	0.5	1.0	mA	
	During A/D, D/A conversion		—	2.0	5.0		
	Idle		—	0.01	5.0		μA
Analog power supply voltage* ¹		AV_{CC}	2.7	—	5.5	V	Operating
			2.0	—	5.5		Idle/not used
RAM standby voltage		V_{RAM}	2.0	—	—	V	

Notes: 1. Do not leave the AV_{CC} , AV_{ref} , and AV_{SS} pins open even if the A/D converter and D/A converter are not used.

Even if the A/D converter and D/A converter are not used, apply a value in the range 2.0 V to 5.5 V to AV_{CC} and AV_{ref} pins by connection to the power supply (V_{CC}), or some other method. Ensure that $AV_{ref} \leq AV_{CC}$.

- P67 to P60 include supporting module inputs multiplexed on those pins.
- $\overline{IRQ2}$ includes the \overline{ADTRG} signal multiplexed on that pin.

4. P52/SCK0/SCL0 and P97/SDA0 are NMOS push-pull outputs.
An external pull-up resistor is necessary to provide high-level output from SCL0 and SDA0 (ICE = 1).
P52/SCK0 and P97 (ICE = 0) high levels are driven by NMOS.
5. When IICS = 0, ICE = 0, and KBIOE = 0. Low-level output when the bus drive function is selected is determined separately.
6. The upper limit of the port 6 applied voltage is $V_{CC} + 0.3 \text{ V}$ when CIN input is not selected, and the lower of $V_{CC} + 0.3 \text{ V}$ and $AV_{CC} + 0.3 \text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
7. The upper limit of the port A applied voltage is $V_{CCB} + 0.3 \text{ V}$ when CIN input is not selected, and the lower of $V_{CCB} + 0.3 \text{ V}$ and $AV_{CC} + 0.3 \text{ V}$ when CIN input is selected. When a pin is in output mode, the output voltage is equivalent to the applied voltage.
8. The port A characteristics depend on V_{CCB} , and the other pins characteristics depend on V_{CC} .
9. The operating supply voltage range specification for the F-ZTAT (low-voltage) version is under investigation. Ranges of $V_{CC} = 3.0$ to 3.6 V and $T_a = 0$ to $+75^\circ\text{C}$ are planned for flash memory programming/erasing.
10. Current dissipation values are for $V_{IH} \text{ min} = V_{CC} - 0.5 \text{ V}$, $V_{CCB} - 0.5 \text{ V}$, and $V_{IL} \text{ max} = 0.5 \text{ V}$ with all output pins unloaded and the on-chip pull-up MOSs in the off state.
11. The values are for $V_{RAM} \leq V_{CC} < 2.7 \text{ V}$, $V_{IH} \text{ min} = V_{CC} \times 0.9$, $V_{CCB} \times 0.9$, and $V_{IL} \text{ max} = 0.3 \text{ V}$.

Table 25.3 Permissible Output Currents

– Preliminary –

Conditions: $V_{CC} = 4.0\text{ V to }5.5\text{ V}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications), $T_a = -40\text{ to }+85^\circ\text{C}$ (wide-range specifications)

Item		Symbol	Min	Typ	Max	Unit
Permissible output low current (per pin)	SCL1, SCL0, SDA1, SDA0, PS2AC to PS2CC, PS2AD to PS2CD, PA7 to PA4 (bus drive function selected)	I_{OL}	—	—	20	mA
	Ports 1, 2, 3		—	—	10	mA
	$\overline{\text{RESO}}$		—	—	3	mA
	Other output pins		—	—	2	mA
Permissible output low current (total)	Total of ports 1, 2, and 3	$\sum I_{OL}$	—	—	80	mA
	Total of all output pins, including the above		—	—	120	mA
Permissible output high current (per pin)	All output pins	$-I_{OH}$	—	—	2	mA
Permissible output high current (total)	Total of all output pins	$\sum -I_{OH}$	—	—	40	mA

- Notes: 1. To protect chip reliability, do not exceed the output current values in table 25.3.
 2. When driving a Darlington pair or LED, always insert a current-limiting resistor in the output line, as show in figures 25.1 and 25.2.

Table 25.3 Permissible Output Currents (cont)**– Preliminary –**

Conditions: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item		Symbol	Min	Typ	Max	Unit
Permissible output low current (per pin)	SCL1, SCL0, SDA1, SDA0, PS2AC to PS2CC, PS2AD to PS2CD, PA7 to PA4 (bus drive function selected)	I_{OL}	—	—	10	mA
	Ports 1, 2, 3		—	—	2	mA
	RESO		—	—	1	mA
	Other output pins		—	—	1	mA
Permissible output low current (total)	Total of ports 1, 2, and 3	$\sum I_{OL}$	—	—	40	mA
	Total of all output pins, including the above		—	—	60	mA
Permissible output high current (per pin)	All output pins	$-I_{OH}$	—	—	2	mA
Permissible output high current (total)	Total of all output pins	$\sum -I_{OH}$	—	—	30	mA

Notes: 1. To protect chip reliability, do not exceed the output current values in table 25.3.

2. When driving a Darlington pair or LED, always insert a current-limiting resistor in the output line, as show in figures 25.1 and 25.2.

Conditions: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$

Applicable Pins: SCL1, SCL0, SDA1, SDA0 (bus drive function selected)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Schmitt trigger input voltage	V_T^-	$V_{CC} \times 0.3$	—	—	V	$V_{CC} = 2.7\text{ V to }5.5\text{ V}$
	V_T^+	—	—	$V_{CC} \times 0.7$		$V_{CC} = 2.7\text{ V to }5.5\text{ V}$
	$V_T^+ - V_T^-$	$V_{CC} \times 0.05$	—	—		$V_{CC} = 2.7\text{ V to }5.5\text{ V}$
Input high voltage	V_{IH}	$V_{CC} \times 0.7$	—	$V_{CC} + 0.5$	V	$V_{CC} = 2.7\text{ V to }5.5\text{ V}$
Input low voltage	V_{IL}	-0.5	—	$V_{CC} \times 0.3$		$V_{CC} = 2.7\text{ V to }5.5\text{ V}$
Output low voltage	V_{OL}	—	—	0.5	V	$I_{OL} = 16\text{ mA}$, $V_{CC} = 4.5\text{ V to }5.5\text{ V}$
				0.5		$I_{OL} = 8\text{ mA}$
				0.4		$I_{OL} = 3\text{ mA}$
Input capacitance	C_{in}	—	—	20	pF	$V_{in} = 0\text{ V}$, $f = 1\text{ MHz}$, $T_a = 25^\circ\text{C}$
Three-state leakage current (off state)	$ I_{TSI} $	—	—	1.0	μA	$V_{in} = 0.5\text{ to }V_{CC} - 0.5\text{ V}$
SCL, SDA output fall time	t_{of}	$20 + 0.1Cb$	—	250	ns	$V_{CC} = 2.7\text{ V to }5.5\text{ V}$

 Conditions: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $T_a = -20\text{ to }+75^\circ\text{C}$

Applicable Pins: PS2AC, PS2AD, PS2BC, PS2BD, PS2CC, PS2CD, PA7 to PA4 (bus drive function selected)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Output low voltage	V_{OL}	—	—	0.8	V	$I_{OL} = 16\text{ mA}$, $V_{CCB} = 4.5\text{ V to }5.5\text{ V}$
				0.5		$I_{OL} = 8\text{ mA}$
				0.4		$I_{OL} = 3\text{ mA}$

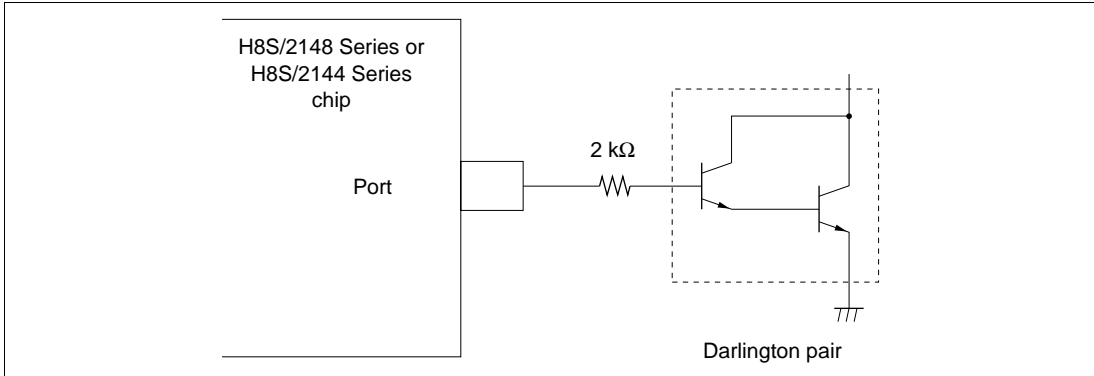


Figure 25.1 Darlington Pair Drive Circuit (Example)

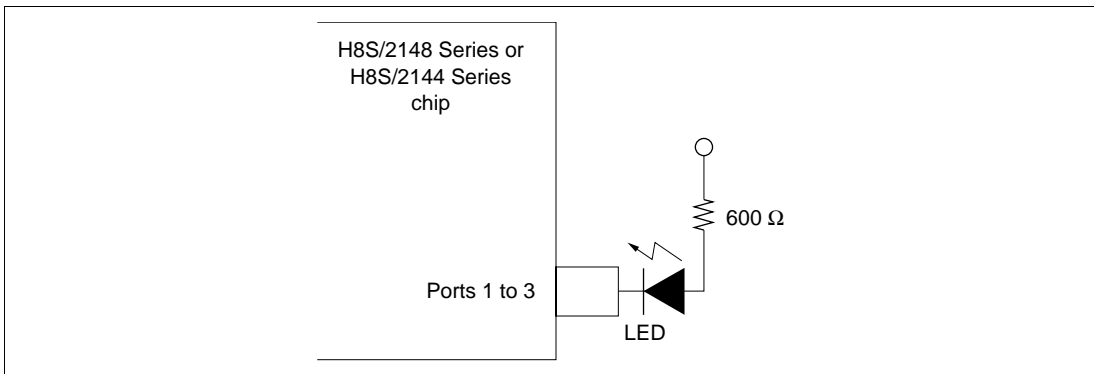


Figure 25.2 LED Drive Circuit (Example)

25.3 AC Characteristics

Figure 25.3 shows the test conditions for the AC characteristics.

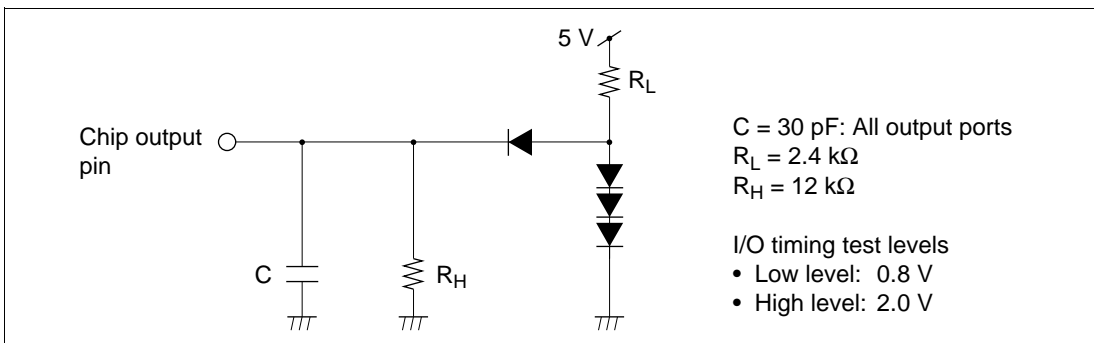


Figure 25.3 Output Load Circuit

25.3.1 Clock Timing

Table 25.5 shows the clock timing. The clock timing specified here covers clock (ϕ) output and clock pulse generator (crystal) and external clock input (EXTAL pin) oscillation settling times. For details of external clock input (EXTAL pin and EXCL pin) timing, see section 23, Clock Pulse Generator. The H8S/2144 Series does not support the VCCB pin function, so V_{CCB} should be read as V_{CC} in the tables for this series.

Table 25.5 Clock Timing

– Preliminary –

Condition A: V_{CC} = 5.0 V ± 10%, V_{CCB} = 5.0 V ± 10%, V_{SS} = 0 V, ϕ = 2 MHz to maximum operating frequency, T_a = –20 to +75°C (regular specifications),
T_a = –40 to +85°C (wide-range specifications)

Condition B: V_{CC} = 4.0 V to 5.5V, V_{CCB} = 4.0 V to 5.5 V, V_{SS} = 0 V, ϕ = 2 MHz to maximum operating frequency, T_a = –20 to +75°C (regular specifications),
T_a = –40 to +85°C (wide-range specifications)

Condition C: V_{CC} = 2.7 V to 5.5V, V_{CCB} = 2.7 V to 5.5 V, V_{SS} = 0 V, ϕ = 2 MHz to maximum operating frequency, T_a = –20 to +75°C (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions
		20 MHz		16 MHz		10 MHz			
Clock cycle time	t _{cyt}	50	500	62.5	500	100	500	ns	Figure 25.4
Clock high pulse width	t _{CH}	17	—	20	—	30	—	ns	Figure 25.4
Clock low pulse width	t _{CL}	17	—	20	—	30	—	ns	
Clock rise time	t _{Cr}	—	8	—	10	—	20	ns	
Clock fall time	t _{Cf}	—	8	—	10	—	20	ns	
Oscillation settling time at reset (crystal)	t _{OSC1}	10	—	10	—	20	—	ms	Figure 25.5 Figure 25.6
Oscillation settling time in software standby (crystal)	t _{OSC2}	8	—	8	—	8	—	ms	
External clock output stabilization delay time	t _{DEXT}	500	—	500	—	500	—	μs	

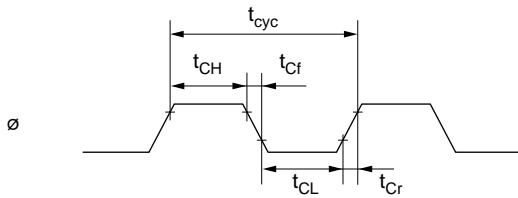


Figure 25.4 System Clock Timing

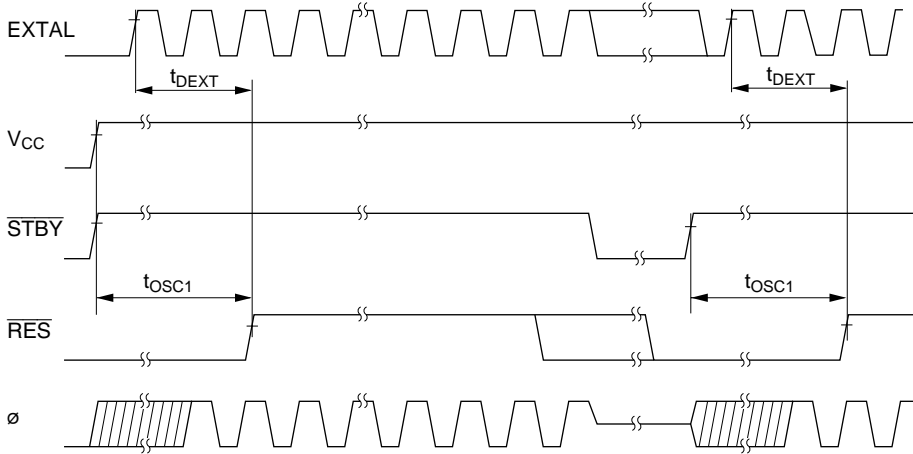


Figure 25.5 Oscillation Settling Timing

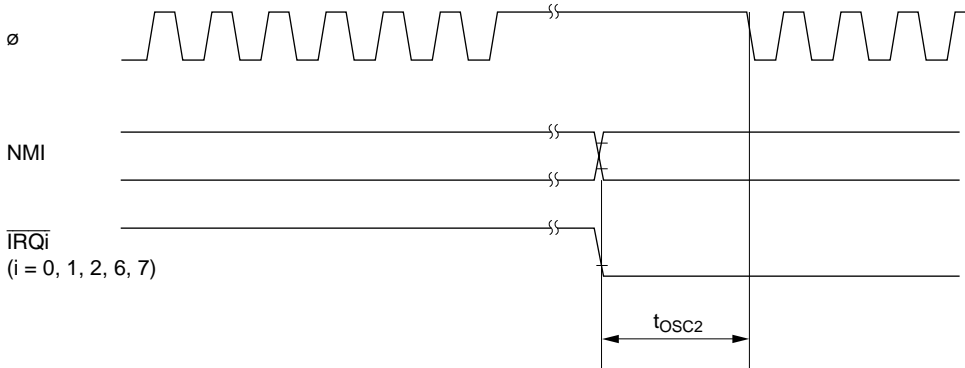


Figure 25.6 Oscillation Setting Timing (Exiting Software Standby Mode)

25.3.2 Control Signal Timing

Table 25.6 shows the control signal timing. The only external interrupts that can operate on the subclock ($\phi = 32.768$ kHz) are NMI and IRQ0, 1, 2, 6, and 7.

Table 25.6 Control Signal Timing

– Preliminary –

Condition A: $V_{CC} = 5.0$ V \pm 10%, $V_{CCB} = 5.0$ V \pm 10%, $V_{SS} = 0$ V, $\phi = 32.768$ kHz, 2 MHz to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0$ V to 5.5V, $V_{CCB} = 4.0$ V to 5.5 V, $V_{SS} = 0$ V, $\phi = 32.768$ kHz, 2 MHz to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7$ V to 5.5V, $V_{CCB} = 2.7$ V to 5.5 V, $V_{SS} = 0$ V, $\phi = 32.768$ kHz, 2 MHz to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions
		20 MHz		16 MHz		10 MHz			
		Min	Max	Min	Max	Min	Max		
$\overline{\text{RES}}$ setup time	t_{RESS}	200	—	200	—	300	—	ns	Figure 25.7
$\overline{\text{RES}}$ pulse width	t_{RESW}	20	—	20	—	20	—	t_{cyc}	
NMI setup time (NMI)	t_{NMIS}	150	—	150	—	250	—	ns	Figure 25.8
NMI hold time (NMI)	t_{NMIH}	10	—	10	—	10	—		
NMI pulse width (exiting software standby mode)	t_{NMIW}	200	—	200	—	200	—	ns	
IRQ setup time (IRQ7 to IRQ0)	t_{IRQS}	150	—	150	—	250	—	ns	
IRQ hold time (IRQ7 to IRQ0)	t_{IRQH}	10	—	10	—	10	—	ns	
IRQ pulse width (IRQ7, IRQ6, IRQ2 to IRQ0) (exiting software standby mode)	t_{IRQW}	200	—	200	—	200	—	ns	

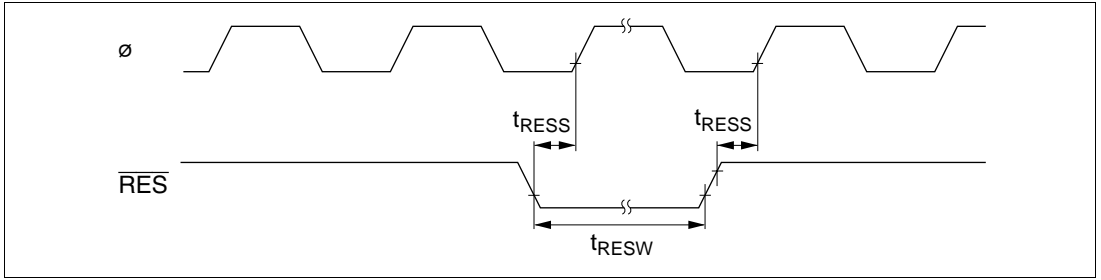


Figure 25.7 Reset Input Timing

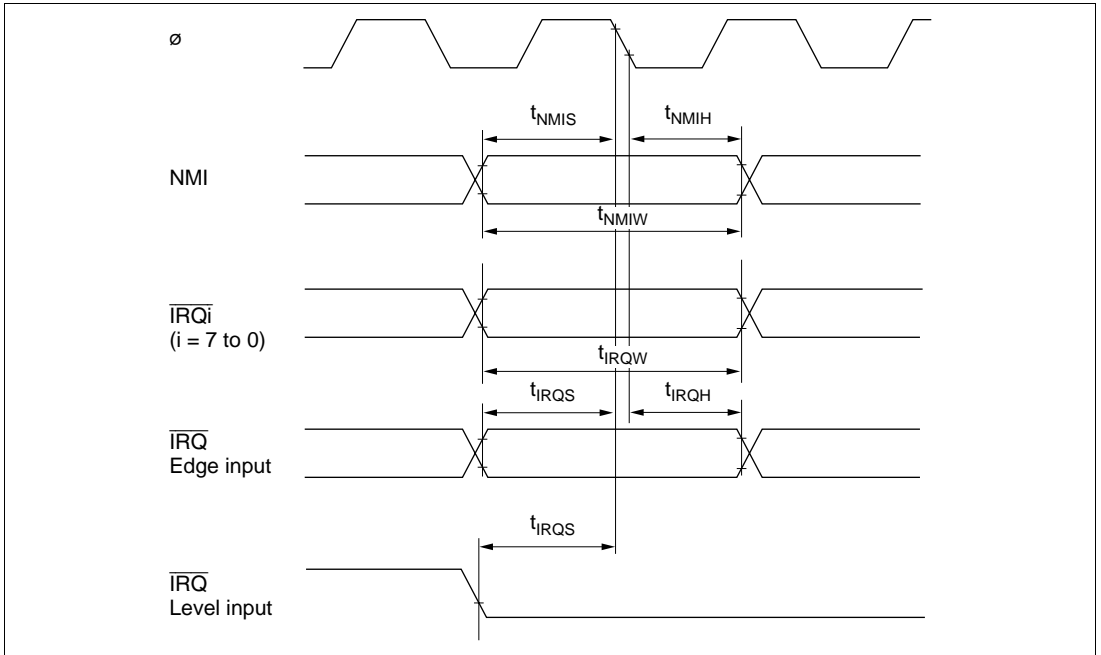


Figure 25.8 Interrupt Input Timing

25.3.3 Bus Timing

Table 25.7 shows the bus timing. Operation in external expansion mode is not guaranteed when operating on the subclock ($\phi = 32.768$ kHz).

Table 25.7 Bus Timing

– Preliminary –

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{CCB} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V}$ to 5.5 V , $V_{CCB} = 4.0 \text{ V}$ to 5.5 V , $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7 \text{ V}$ to 5.5 V , $V_{CCB} = 2.7 \text{ V}$ to 5.5 V , $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions
		20 MHz		16 MHz		10 MHz			
		Min	Max	Min	Max	Min	Max		
Address delay time	t_{AD}	—	20	—	30	—	40	ns	Figure 25.9 to figure 25.13
Address setup time	t_{AS}	$0.5 \times t_{cyc} - 15$	—	$0.5 \times t_{cyc} - 20$	—	$0.5 \times t_{cyc} - 30$	—	ns	
Address hold time	t_{AH}	$0.5 \times t_{cyc} - 10$	—	$0.5 \times t_{cyc} - 15$	—	$0.5 \times t_{cyc} - 20$	—	ns	
\overline{CS} delay time (\overline{IOS})	t_{CSD}	—	20	—	30	—	40	ns	
\overline{AS} delay time	t_{ASD}	—	30	—	45	—	60	ns	
\overline{RD} delay time 1	t_{RSD1}	—	30	—	45	—	60	ns	
\overline{RD} delay time 2	t_{RSD2}	—	30	—	45	—	60	ns	
Read data setup time	t_{RDS}	15	—	20	—	35	—	ns	
Read data hold time	t_{RDH}	0	—	0	—	0	—	ns	

Condition A: $V_{CC} = 5.0\text{ V} \pm 10\%$, $V_{CCB} = 5.0\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0\text{ V}$ to 5.5V , $V_{CCB} = 4.0\text{ V}$ to 5.5 V , $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7\text{ V}$ to 5.5V , $V_{CCB} = 2.7\text{ V}$ to 5.5 V , $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions
		20 MHz		16 MHz		10 MHz			
		Min	Max	Min	Max	Min	Max		
Read data access time 1	t_{ACC1}	—	$1.0 \times t_{cyc} - 30$	—	$1.0 \times t_{cyc} - 40$	—	$1.0 \times t_{cyc} - 60$	ns	Figure 25.9 to figure 25.13
Read data access time 2	t_{ACC2}	—	$1.5 \times t_{cyc} - 25$	—	$1.5 \times t_{cyc} - 35$	—	$1.5 \times t_{cyc} - 50$	ns	
Read data access time 3	t_{ACC3}	—	$2.0 \times t_{cyc} - 30$	—	$2.0 \times t_{cyc} - 40$	—	$2.0 \times t_{cyc} - 60$	ns	
Read data access time 4	t_{ACC4}	—	$2.5 \times t_{cyc} - 25$	—	$2.5 \times t_{cyc} - 35$	—	$2.5 \times t_{cyc} - 50$	ns	
Read data access time 5	t_{ACC5}	—	$3.0 \times t_{cyc} - 30$	—	$3.0 \times t_{cyc} - 40$	—	$3.0 \times t_{cyc} - 60$	ns	
WR delay time 1	t_{WRD1}	—	30	—	45	—	60	ns	
WR delay time 2	t_{WRD2}	—	30	—	45	—	60	ns	
WR pulse width 1	t_{WSW1}	$1.0 \times t_{cyc} - 20$	—	$1.0 \times t_{cyc} - 30$	—	$1.0 \times t_{cyc} - 40$	—	ns	
WR pulse width 2	t_{WSW2}	$1.5 \times t_{cyc} - 20$	—	$1.5 \times t_{cyc} - 30$	—	$1.5 \times t_{cyc} - 40$	—	ns	

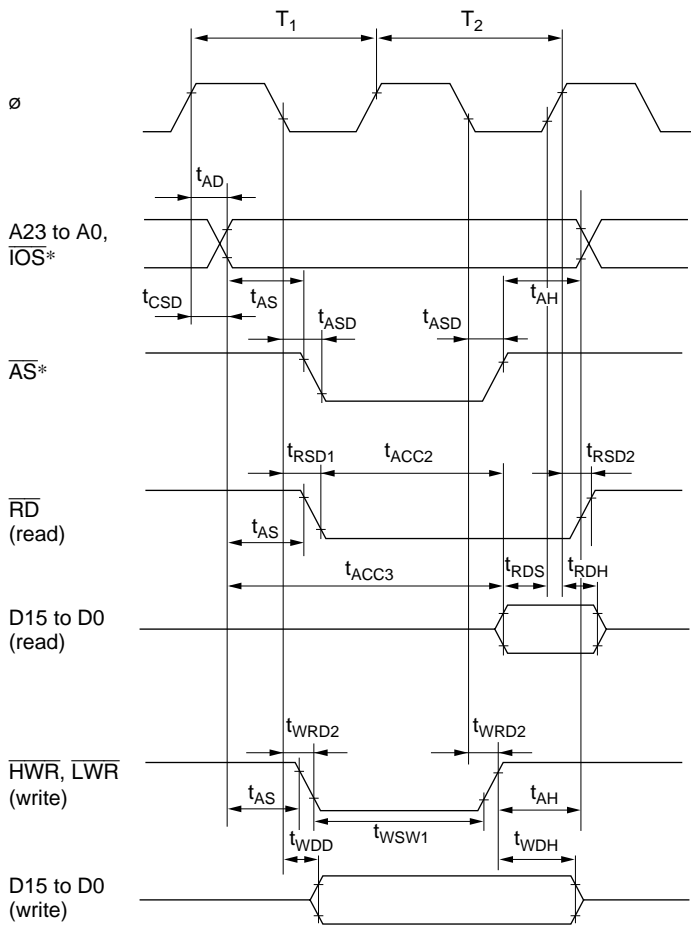
Table 25.7 Bus Timing (cont)**– Preliminary –**

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{CCB} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V}$ to 5.5 V , $V_{CCB} = 4.0 \text{ V}$ to 5.5 V , $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

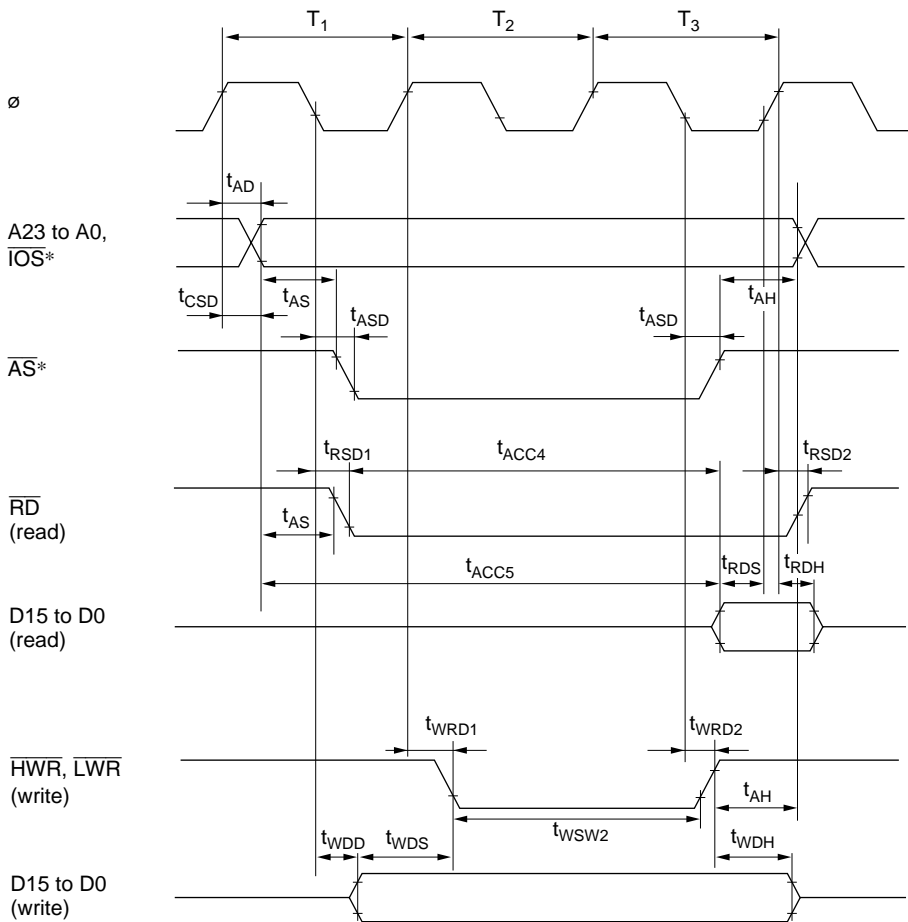
Condition C: $V_{CC} = 2.7 \text{ V}$ to 5.5 V , $V_{CCB} = 2.7 \text{ V}$ to 5.5 V , $V_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions
		20 MHz		16 MHz		10 MHz			
		Min	Max	Min	Max	Min	Max		
Write data delay time	t_{WDD}	—	30	—	45	—	60	ns	Figure 25.9 to figure 25.13
Write data setup time	t_{WDS}	0	—	0	—	0	—	ns	
Write data hold time	t_{WDH}	10	—	15	—	20	—	ns	
WAIT setup time	t_{WTS}	30	—	45	—	60	—	ns	
WAIT hold time	t_{WTH}	5	—	5	—	10	—	ns	



Note: * \overline{AS} and \overline{IOS} are the same pin. The function is selected by the IOSE bit in SYSCR.

Figure 25.9 Basic Bus Timing (Two-State Access)



Note: * \overline{AS} and \overline{IOS} are the same pin. The function is selected by the IOSE bit in SYSCR.

Figure 25.10 Basic Bus Timing (Three-State Access)

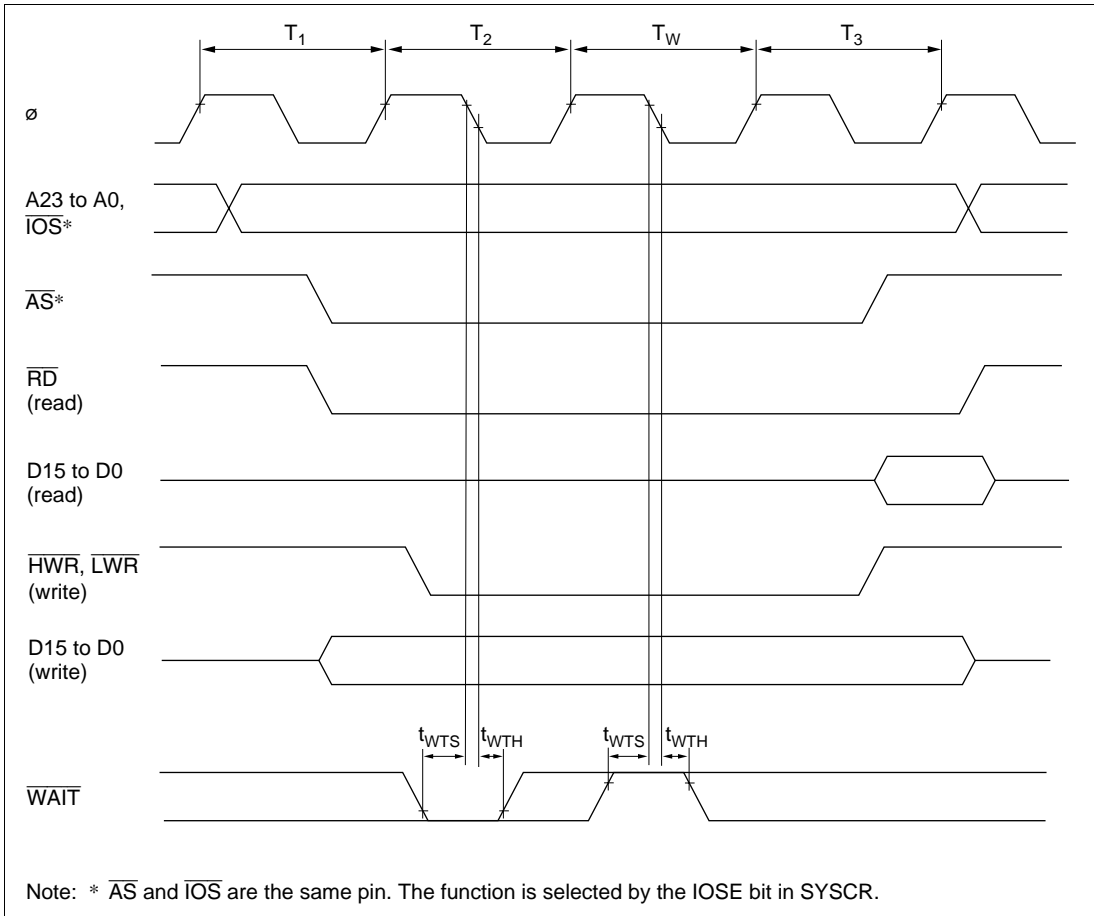


Figure 25.11 Basic Bus Timing (Three-State Access with One Wait State)

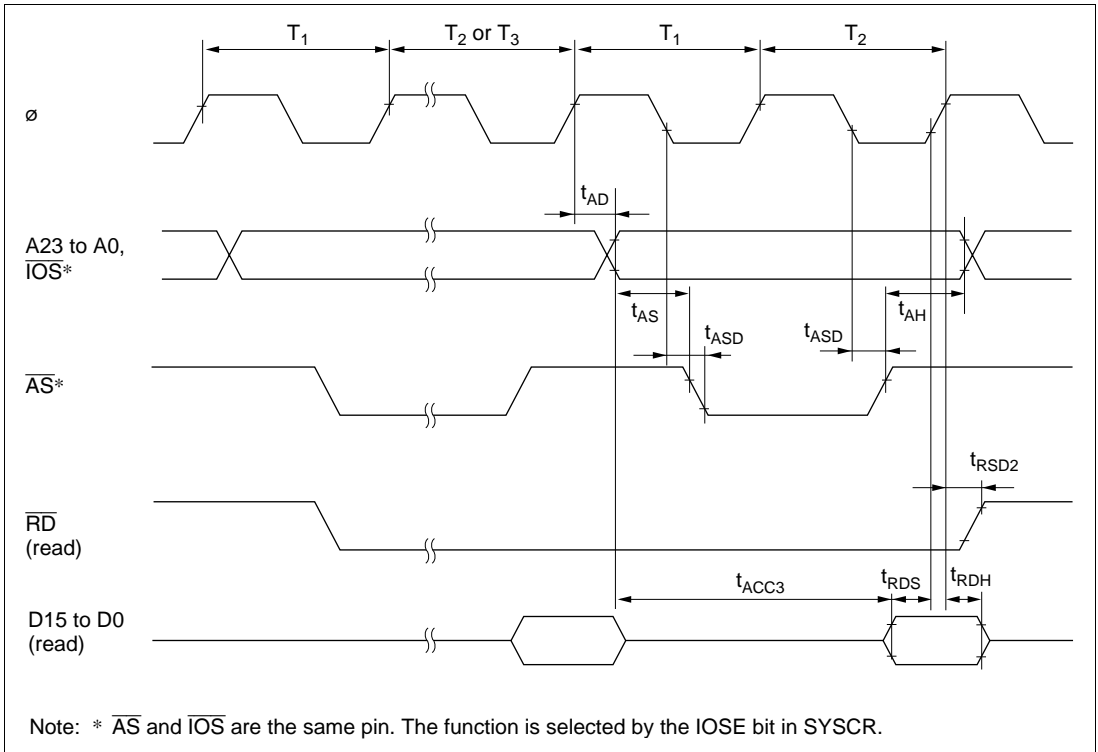
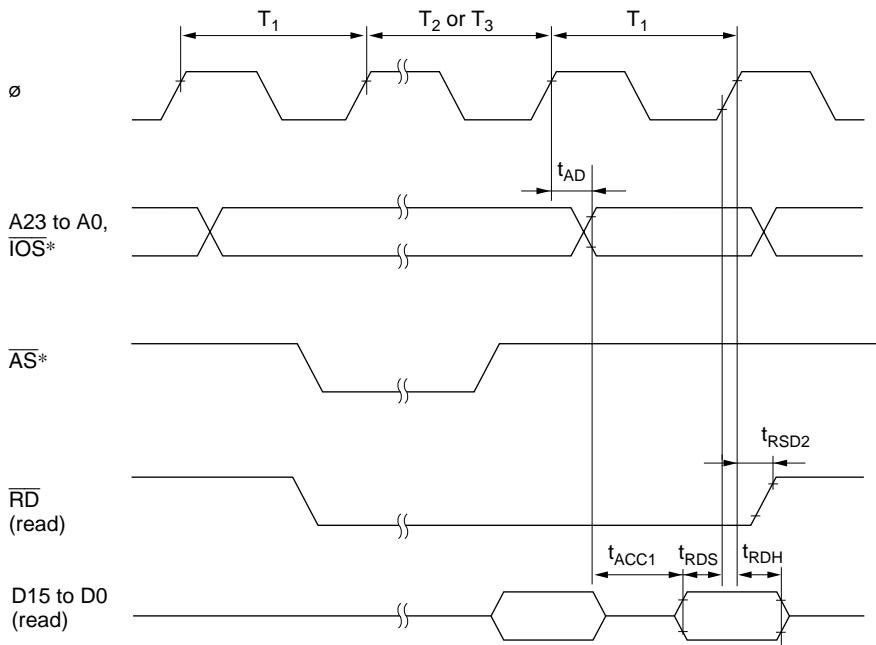


Figure 25.12 Burst ROM Access Timing (Two-State Access)



Note: * \overline{AS} and \overline{IOS} are the same pin. The function is selected by the IOSE bit in SYSCR.

Figure 25.13 Burst ROM Access Timing (One-State Access)

25.3.4 Timing of On-Chip Supporting Modules

Tables 25.8 to 25.10 show the on-chip supporting module timing. The only on-chip supporting modules that can operate in subclock operation ($\phi = 32.768 \text{ kHz}$) are the I/O ports, external interrupts (NMI and IRQ0, 1, 2, 6, and 7), the watchdog timer, and the 8-bit timer (channels 0 and 1).

Table 25.8 Timing of On-Chip Supporting Modules (1) – Preliminary –

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{CCB} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $\phi = 32.768 \text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20 \text{ to } +75^\circ\text{C}$ (regular specifications),
 $T_a = -40 \text{ to } +85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V to } 5.5\text{V}$, $V_{CCB} = 4.0 \text{ V to } 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$, $\phi = 32.768 \text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20 \text{ to } +75^\circ\text{C}$ (regular specifications),
 $T_a = -40 \text{ to } +85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7 \text{ V to } 5.5\text{V}$, $V_{CCB} = 2.7 \text{ V to } 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$, $\phi = 32.768 \text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20 \text{ to } +75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions	
		Min	Max	Min	Max	Min	Max			
I/O ports	Output data delay time	t_{PWD}	—	50	—	50	—	100	ns	Figure 25.14
	Input data setup time	t_{PRS}	30	—	30	—	50	—		
	Input data hold time	t_{PRH}	30	—	30	—	50	—		
FRT	Timer output delay time	t_{FTOD}	—	50	—	50	—	100	ns	Figure 25.15
	Timer input setup time	t_{FTIS}	30	—	30	—	50	—		
	Timer clock input setup time	t_{FTCS}	30	—	30	—	50	—		Figure 25.16
	Timer clock pulse width	Single edge	t_{FTCWH}	1.5	—	1.5	—	1.5	—	t_{cyc}
Both edges		t_{FTCWL}	2.5	—	2.5	—	2.5	—		

Table 25.8 Timing of On-Chip Supporting Modules (1) (cont)
– Preliminary –

Condition A: $V_{CC} = 5.0\text{ V} \pm 10\%$, $V_{CCB} = 5.0\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications),
 $T_a = -40\text{ to }+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0\text{ V to }5.5\text{V}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications),
 $T_a = -40\text{ to }+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7\text{ V to }5.5\text{V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions		
		20 MHz		16 MHz		10 MHz					
		Min	Max	Min	Max	Min	Max				
TMR	Timer output delay time	t_{TMOD}	—	50	—	50	—	100	ns	Figure 25.17	
	Timer reset input setup time	t_{TMRS}	30	—	30	—	50	—		Figure 25.19	
	Timer clock input setup time	t_{TMCS}	30	—	30	—	50	—		Figure 25.18	
	Timer clock pulse width	Single edge	t_{TMCWH}	1.5	—	1.5	—	1.5	—	t_{cyc}	
	Both edges	t_{TMCWL}	2.5	—	2.5	—	2.5	—			
PWM, PWMX	Pulse output delay time	t_{PWOD}	—	50	—	50	—	100	ns	Figure 25.20	
SCI	Input clock cycle	Asynchronous	t_{Scyc}	4	—	4	—	4	—	t_{cyc}	Figure 25.21
		Synchronous		6	—	6	—	6	—		
	Input clock pulse width	t_{SCKW}	0.4	0.6	0.4	0.6	0.4	0.6	t_{Scyc}		
	Input clock rise time	t_{SCKr}	—	1.5	—	1.5	—	1.5	t_{cyc}		
	Input clock fall time	t_{SCKf}	—	1.5	—	1.5	—	1.5			

Table 25.8 Timing of On-Chip Supporting Modules (1) (cont)
– Preliminary –

Condition A: $V_{CC} = 5.0\text{ V} \pm 10\%$, $V_{CCB} = 5.0\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications),
 $T_a = -40\text{ to }+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0\text{ V to }5.5\text{ V}$, $V_{CCB} = 4.0\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications),
 $T_a = -40\text{ to }+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $\phi = 32.768\text{ kHz}^*$, 2 MHz to maximum operating frequency, $T_a = -20\text{ to }+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions	
		20 MHz		16 MHz		10 MHz				
		Min	Max	Min	Max	Min	Max			
SCI	Transmit data delay time (synchronous)	t_{TXD}	—	50	—	50	—	100	ns	Figure 25.22
	Receive data setup time (synchronous)	t_{RXS}	50	—	50	—	100	—	ns	
	Receive data hold time (synchronous)	t_{RXH}	50	—	50	—	100	—	ns	
A/D converter	Trigger input setup time	t_{TRGS}	30	—	30	—	50	—	ns	Figure 25.23
WDT	$\overline{\text{RESO}}$ output delay time	t_{RESD}	—	100	—	120	—	200	ns	Figure 25.24
	$\overline{\text{RESO}}$ output pulse width	t_{RESOW}	132	—	132	—	132	—	t_{cyc}	

Note: * Only supporting modules that can be used in subclock operation

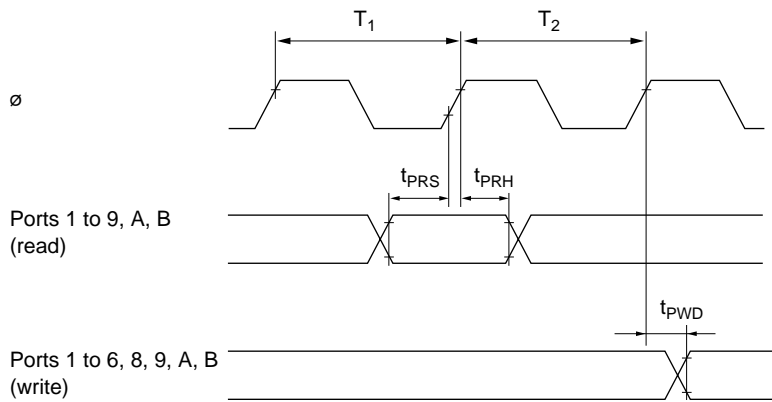


Figure 25.14 I/O Port Input/Output Timing

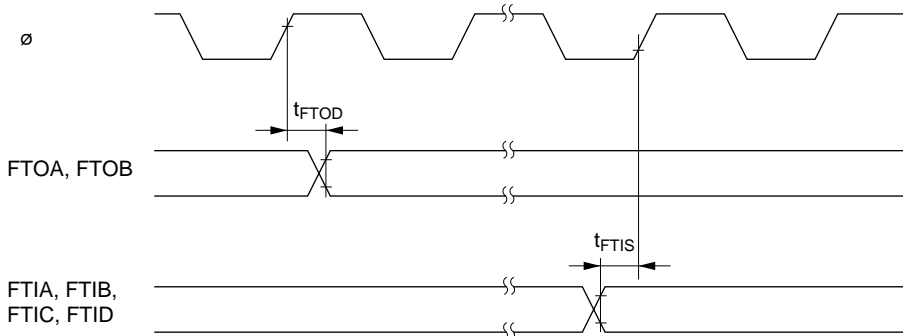


Figure 25.15 FRT Input/Output Timing

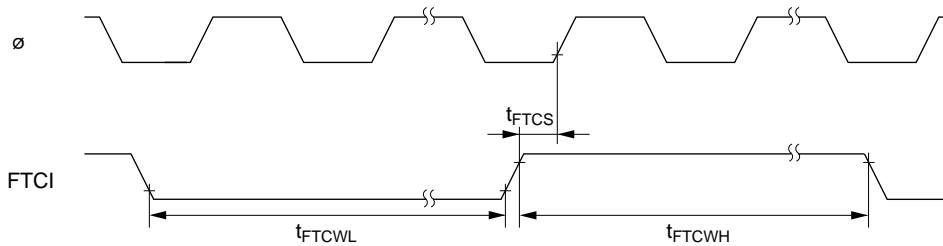


Figure 25.16 FRT Clock Input Timing

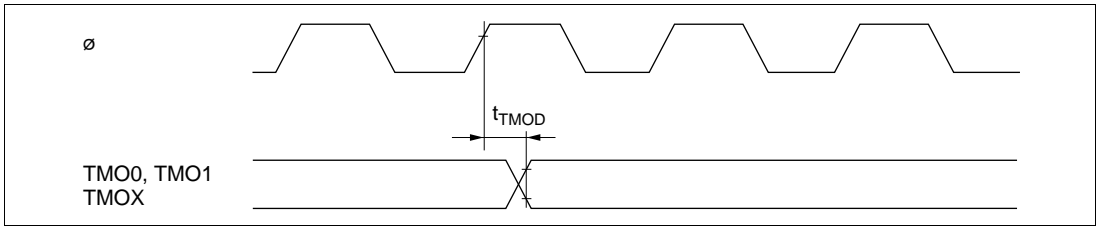


Figure 25.17 8-Bit Timer Output Timing

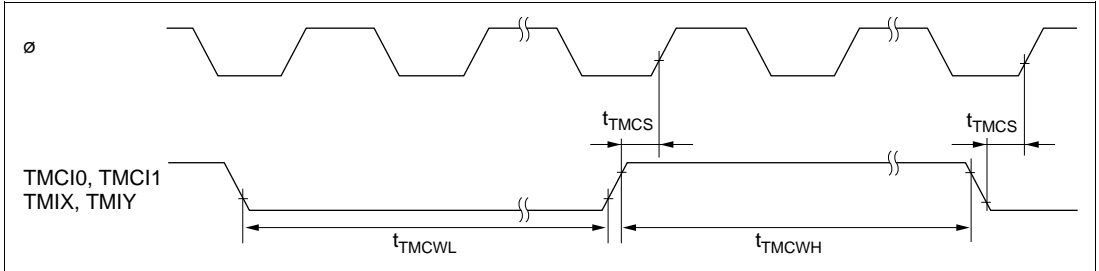


Figure 25.18 8-Bit Timer Clock Input Timing

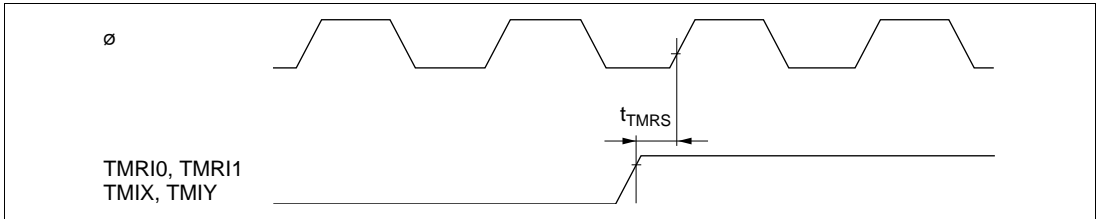


Figure 25.19 8-Bit Timer Reset Input Timing

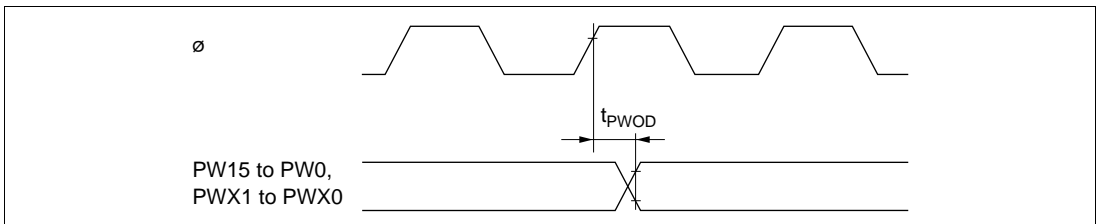


Figure 25.20 PWM, PWMX Output Timing

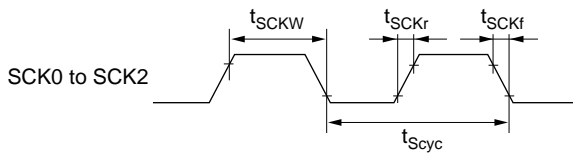


Figure 25.21 SCK Clock Input Timing

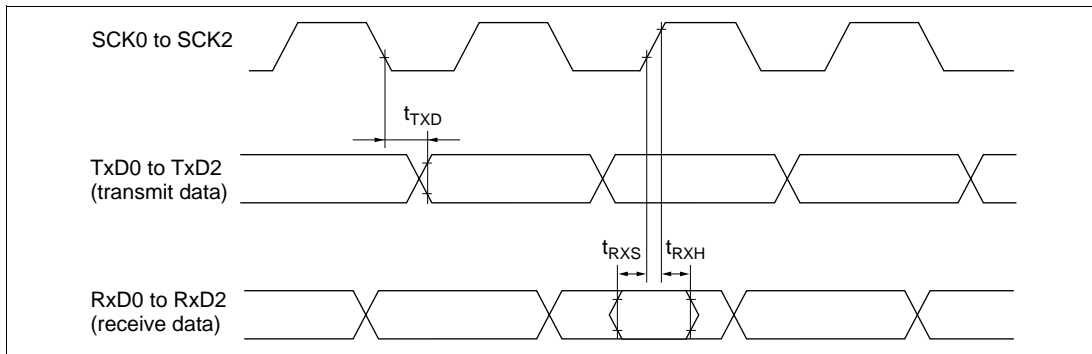


Figure 25.22 SCI Input/Output Timing (Synchronous Mode)

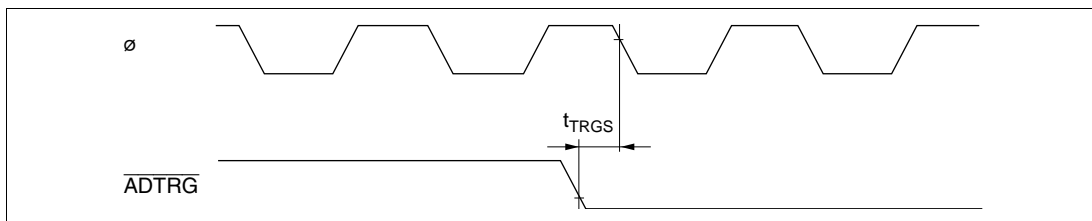


Figure 25.23 A/D Converter External Trigger Input Timing

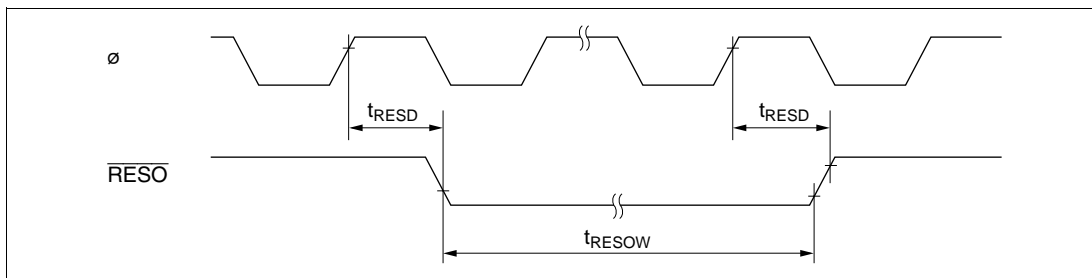


Figure 25.24 WDT Output Timing ($\overline{\text{RESO}}$)

Table 25.8 Timing of On-Chip Supporting Modules (2)

– Preliminary –

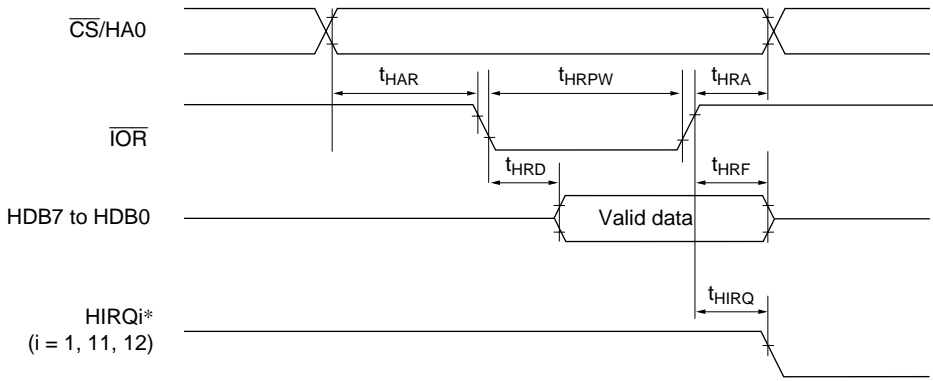
Condition A: $V_{CC} = 5.0\text{ V} \pm 10\%$, $V_{CCB} = 5.0\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0\text{ V}$ to 5.5 V , $V_{CCB} = 4.0\text{ V}$ to 5.5 V , $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7\text{ V}$ to 5.5 V , $V_{CCB} = 2.7\text{ V}$ to 5.5 V , $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz}$ to maximum operating frequency, $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Symbol	Condition A		Condition B		Condition C		Unit	Test Conditions	
		20 MHz		16 MHz		10 MHz				
		Min	Max	Min	Max	Min	Max			
HIF read cycle	$\overline{\text{CS}}/\text{HA0}$ setup item	t_{HAR}	10	—	10	—	10	—	ns	Figure 25.25
	$\overline{\text{CS}}/\text{HA0}$ hold time	t_{HRA}	10	—	10	—	10	—	ns	
	$\overline{\text{IOR}}$ pulse width	t_{HRPW}	120	—	120	—	220	—	ns	
	HDB delay time	t_{HRD}	—	100	—	100	—	200	ns	
	HDB hold time	t_{HRF}	0	25	0	25	0	40	ns	
	HIRQ delay time	t_{HIRQ}	—	120	—	120	—	200	ns	
HIF write cycle	$\overline{\text{CS}}/\text{HA0}$ setup item	t_{HAW}	10	—	10	—	10	—	ns	
	$\overline{\text{CS}}/\text{HA0}$ hold time	t_{HWA}	10	—	10	—	10	—	ns	
	$\overline{\text{IOW}}$ pulse width	t_{HWPW}	60	—	60	—	100	—	ns	
	HDB setup time	Fast A20 gate not used	t_{HDW}	30	—	30	—	50	—	ns
		Fast A20 gate used		45	—	55	—	85	—	ns
	HDB hold time	t_{HWD}	15	—	15	—	25	—	ns	
GA20 delay time	t_{HGA}	—	90	—	90	—	180	ns		

Host interface read timing



Note: * The rising edge timing is the same as the port 4 output timing. See figure 25.14.

Host interface write timing

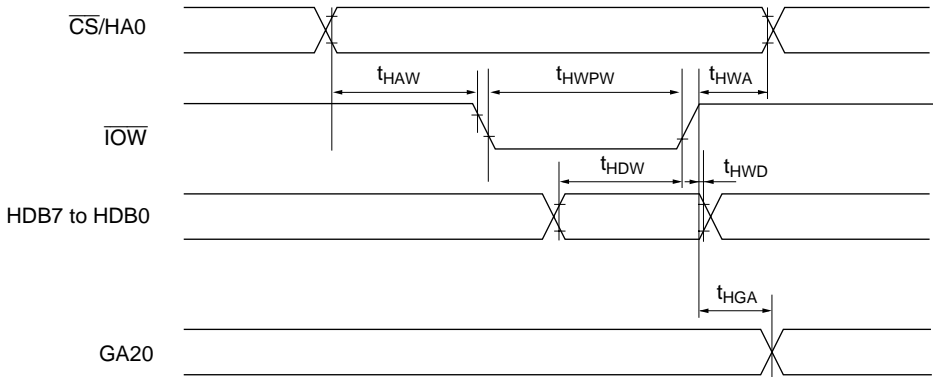


Figure 25.25 Host Interface Timing

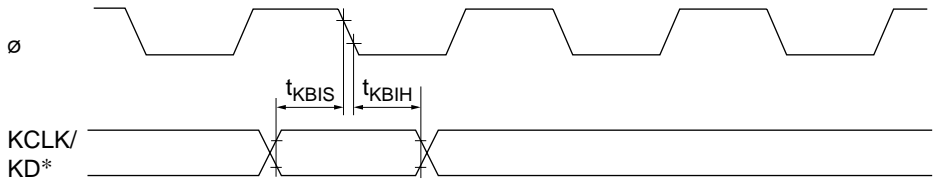
Table 25.9 Keyboard Buffer Controller Timing

– Preliminary –

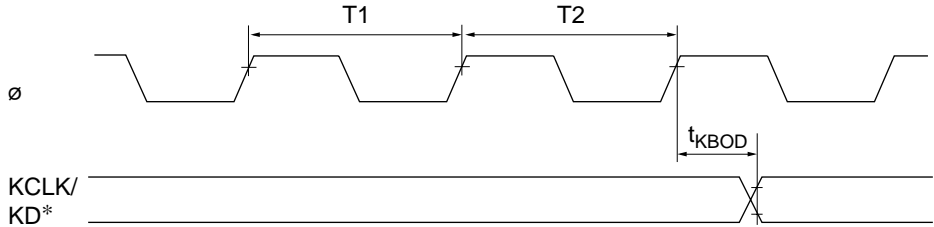
Conditions: $V_{CC} = 2.7\text{ V to }5.5\text{ V}$, $V_{CCB} = 2.7\text{ V to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$, $\phi = 2\text{ MHz to maximum operating frequency}$, $T_a = -20\text{ to }+75^\circ\text{C}$

Item	Symbol	Ratings			Unit	Test Conditions	Notes
		Min	Typ	Max			
KCLK, KD fall time	t_{KBF}	$20 + 0.1Cb$	—	250	ns		Figure 25.26
KCLK, KD input data hold time	t_{KBIH}	150	—	—	ns		
KCLK, KD input data setup time	t_{KBIS}	150	—	—	ns		
KCLK, KD output delay time	t_{KBOD}	—	—	450	ns		
KCLK, KD capacitive load	Cb	—	—	400	pF		

1. Reception



2. Transmission (a)



Transmission (b)



Note: ϕ shown here is the clock scaled by 1/N when the operating mode is active medium-speed mode.

* KCLK: PS2AC to PS2CC

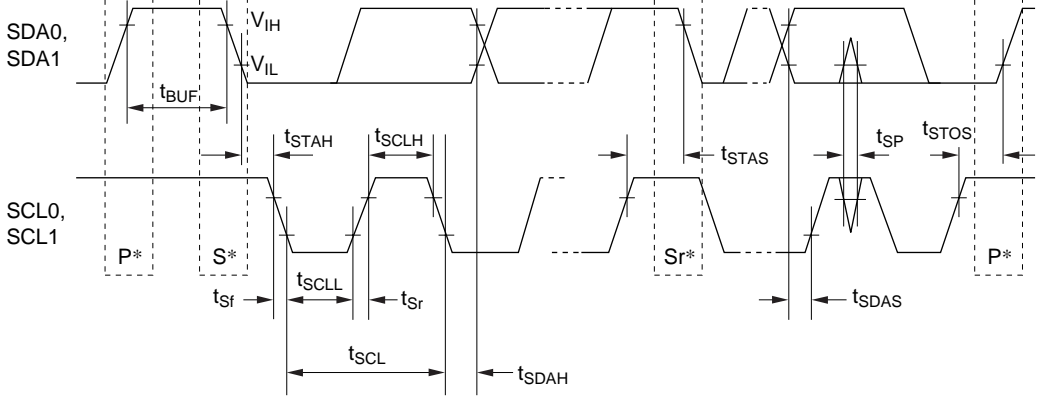
KD: PS2AD to PS2CD

Figure 25.26 Keyboard Buffer Controller Timing

Conditions: $V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$, $\phi = 5 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20 \text{ to } +75^\circ\text{C}$

Item	Symbol	Ratings			Unit	Test Conditions	Notes
		Min	Typ	Max			
SCL clock cycle time	t_{SCL}	12	—	—	t_{cyc}		Figure 25.27
SCL clock high pulse width	t_{SCLH}	3	—	—	t_{cyc}		
SCL clock low pulse width	t_{SCLL}	5	—	—	t_{cyc}		
SCL, SDA input rise time	t_{Sr}	—	—	7.5*	t_{cyc}		
SCL, SDA input fall time	t_{Sf}	—	—	300	ns		
SCL, SDA input spike pulse elimination time	t_{SP}	—	—	1	t_{cyc}		
SDA input bus free time	t_{BUF}	5	—	—	t_{cyc}		
Start condition input hold time	t_{STAH}	3	—	—	t_{cyc}		
Retransmission start condition input setup time	t_{STAS}	3	—	—	t_{cyc}		
Stop condition input setup time	t_{STOS}	3	—	—	t_{cyc}		
Data input setup time	t_{SDAS}	0.5	—	—	t_{cyc}		
Data input hold time	t_{SDAH}	0	—	—	ns		
SCL, SDA capacitive load	C_b	—	—	400	pF		

Note: * $17.5t_{cyc}$ can be set according to the clock selected for use by the I²C module. For details, see section 16.4, Usage Notes.



Note: * S, P, and Sr indicate the following conditions.

S: Start condition

P: Stop condition

Sr: Retransmission start condition

Figure 25.27 I²C Bus Interface Input/Output Timing (Option)

25.4 A/D Conversion Characteristics

Tables 25.11 and 25.12 list the A/D conversion characteristics.

Table 25.11 A/D Conversion Characteristics
(AN7 to AN0 Input: 134/266-State Conversion)

– Preliminary –

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{ref} = 4.5 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{ref} = 4.0 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{ref} = 2.7 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Condition A			Condition B			Condition C			Unit
	20 MHz			16 MHz			10 MHz			
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Resolution	10	10	10	10	10	10	10	10	10	Bits
Conversion time	—	—	6.7	—	—	8.4	—	—	13.4	μs
Analog input capacitance	—	—	20	—	—	20	—	—	20	pF
Permissible signal-source impedance	—	—	10^{*3}	—	—	10^{*3}	—	—	10^{*1}	k Ω
			5^{*4}			5^{*4}			5^{*2}	
Nonlinearity error	—	—	± 3.0	—	—	± 3.0	—	—	± 7.0	LSB
Offset error	—	—	± 3.5	—	—	± 3.5	—	—	± 7.5	LSB
Full-scale error	—	—	± 3.5	—	—	± 3.5	—	—	± 7.5	LSB
Quantization error	—	—	± 0.5	—	—	± 0.5	—	—	± 0.5	LSB
Absolute accuracy	—	—	± 4.0	—	—	± 4.0	—	—	± 8.0	LSB

- Notes: 1. When $4.0 \text{ V} \leq AV_{CC} \leq 5.5 \text{ V}$
2. When $2.7 \text{ V} \leq AV_{CC} < 4.0 \text{ V}$
3. When conversion time $\geq 11.17 \mu\text{s}$ (CKS = 1 and $\phi \leq 12 \text{ MHz}$, or CKS = 0)
4. When conversion time $< 11.17 \mu\text{s}$ (CKS = 1 and $\phi > 12 \text{ MHz}$)

Table 25.12 A/D Conversion Characteristics
(CIN15 to CIN0 Input: 134/266-State Conversion)
– Preliminary –

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{ref} = 4.5 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{ref} = 4.0 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{ref} = 2.7 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item	Condition A			Condition B			Condition C			Unit
	20 MHz			16 MHz			10 MHz			
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Resolution	10	10	10	10	10	10	10	10	10	Bits
Conversion time	—	—	6.7	—	—	8.4	—	—	13.4	μs
Analog input capacitance	—	—	20	—	—	20	—	—	20	pF
Permissible signal-source impedance	—	—	10^{*3}	—	—	10^{*3}	—	—	10^{*1}	k Ω
			5^{*4}			5^{*4}			5^{*2}	
Nonlinearity error	—	—	± 5.0	—	—	± 5.0	—	—	± 11.0	LSB
Offset error	—	—	± 5.5	—	—	± 5.5	—	—	± 11.5	LSB
Full-scale error	—	—	± 5.5	—	—	± 5.5	—	—	± 11.5	LSB
Quantization error	—	—	± 0.5	—	—	± 0.5	—	—	± 0.5	LSB
Absolute accuracy	—	—	± 6.0	—	—	± 6.0	—	—	± 12.0	LSB

Notes: 1. When $4.0 \text{ V} \leq AV_{CC} \leq 5.5 \text{ V}$

2. When $2.7 \text{ V} \leq AV_{CC} < 4.0 \text{ V}$

3. When conversion time $\geq 11.17 \mu\text{s}$ (CKS = 1 and $\phi \leq 12 \text{ MHz}$, or CKS = 0)

4. When conversion time $< 11.17 \mu\text{s}$ (CKS = 1 and $\phi > 12 \text{ MHz}$)

25.5 D/A Conversion Characteristics

Table 25.13 lists the D/A conversion characteristics.

Table 25.13 D/A Conversion Characteristics

– Preliminary –

Condition A: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{ref} = 4.5 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition B: $V_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{CC} = 4.0 \text{ V}$ to 5.5 V , $AV_{ref} = 4.0 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications),
 $T_a = -40$ to $+85^\circ\text{C}$ (wide-range specifications)

Condition C: $V_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{CC} = 2.7 \text{ V}$ to 5.5 V , $AV_{ref} = 2.7 \text{ V}$ to AV_{CC}
 $V_{SS} = AV_{SS} = 0 \text{ V}$, $\phi = 2 \text{ MHz}$ to maximum operating frequency,
 $T_a = -20$ to $+75^\circ\text{C}$ (regular specifications)

Item		Condition A			Condition B			Condition C			Unit
		20 MHz			16 MHz			10 MHz			
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Resolution		8	8	8	8	8	8	8	8	8	Bits
Conversion time	With 20 pF load capacitance	—	—	10	—	—	10	—	—	10	μs
Absolute accuracy	With 2 M Ω load resistance	—	± 1.0	± 1.5	—	± 1.0	± 1.5	—	± 2.0	± 3.0	LSB
	With 4 M Ω load resistance	—	—	± 1.0	—	—	± 1.0	—	—	± 2.0	

25.6 Flash Memory Characteristics

Table 25.14 shows the flash memory characteristics.

Table 25.14 Flash Memory Characteristics (5 V Version)*8

Conditions: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = AV_{SS} = 0 \text{ V}$,
 $T_a = 0 \text{ to } +75^\circ\text{C}$ (Programming/erasing operating temperature)

Item	Symbol	Min	Typ	Max	Unit	Test Condition	
Programming time*1,*2,*4	tP	—	10	200	ms/ 32 bytes		
Erase time*1,*3,*5	tE	—	100	1200	ms/ block		
Reprogramming count	N_{WEC}	—	—	100	Times		
Programming	Wait time after SWE-bit setting*1	x	10	—	—	μs	
	Wait time after PSU-bit setting*1	y	50	—	—	μs	
	Wait time after P-bit setting*1,*4	z	150	—	200	μs	
	Wait time after P-bit clear*1	α	10	—	—	μs	
	Wait time after PSU-bit clear*1	β	10	—	—	μs	
	Wait time after PV-bit setting*1	γ	4	—	—	μs	
	Wait time after dummy write*1	ε	2	—	—	μs	
	Wait time after PV-bit clear*1	η	4	—	—	μs	
	Maximum programming count*1,*4,*5	N	—	—	1000	Times	tP = 200 μs

Table 25.14 Flash Memory Characteristics (5 V Version)*⁸ (cont)

Conditions: $V_{CC} = 5.0 \text{ V} \pm 10\%$, $AV_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = AV_{SS} = 0 \text{ V}$,
 $T_a = 0 \text{ to } +75^\circ\text{C}$ (Programming/erasing operating temperature)

Item		Symbol	Min	Typ	Max	Unit	Test Condition
Erase	Wait time after SWE-bit setting* ¹	x	10	—	—	μs	
	Wait time after ESU-bit setting* ¹	y	200	—	—	μs	
	Wait time after E-bit setting* ^{1,*6}	z	5	—	10	ms	
	Wait time after E-bit clear* ¹	α	10	—	—	μs	
	Wait time after ESU-bit clear* ¹	β	10	—	—	μs	
	Wait time after EV-bit setting* ¹	γ	20	—	—	μs	
	Wait time after dummy write* ¹	ε	2	—	—	μs	
	Wait time after EV-bit clear* ¹	η	5	—	—	μs	
	Maximum erase count* ^{1,*6,*7}	N	—	—	120	Times	$tE = 10 \text{ ms}$

- Notes: 1. Set the times according to the program/erase algorithms.
2. Programming time per 32 bytes (Shows the total time the flash memory control register (FLMCR1) is set. It does not include the programming verification time.)
3. Block erase time (Shows the total period for which the E-bit in FLMCR1 is set. It does not include the erase verification time.)
4. Maximum programming time (tP (max)) = wait time after P-bit setting (z) \times maximum programming count (N))
5. Number of times when the wait time after P-bit setting (z) = 200 μs .
 The number of writes should be set according to the actual set value of z to allow programming within the maximum programming time (tP).
6. Maximum erase time (tE (max)) = Wait time after E-bit setting (z) \times maximum erase count (N))
7. Number of times when the wait time after E-bit setting (z) = 10 ms.
 The number of erases should be set according to the actual set value of z to allow erasing within the maximum erase time (tE).
8. Low-voltage version flash memory characteristics will be decided later.

25.7 Usage Note

The F-ZTAT and mask ROM versions have been confirmed as fully meeting the reference values for electrical characteristics shown in this manual. However, actual performance figures, operating margins, noise margins, and other properties may vary due to differences in the manufacturing process, on-chip ROM, layout patterns, etc.

When system evaluation testing is carried out using the F-ZTAT version, the same evaluation tests should also be conducted for the mask ROM version when changing over to that version.

Appendix F Product Code Lineup

Table F.1 H8S/2148 Series and H8S/2144 Series Product Code Lineup — Preliminary —

Product Type			Product Code	Mark Code	Package (Hitachi Package Code)	Notes
H8S/2148 Series	H8S/2148 Mask ROM version	Standard product (5 V version, 4 V version, 3 V version)	HD6432148	HD6432148(***)FA	100-pin FP (FP-100B)	In planning stage
				HD6432148(***)TE	100-pin TFP (TFP-100B)	
		Version with on-chip I ² C bus interface (5 V version, 4 V version, 3 V version)	HD6432148W	HD6432148W(***)FA	100-pin FP (FP-100B)	
				HD6432148W(***)TE	100-pin TFP (TFP-100B)	
	F-ZTAT version	Standard product (5 V/4 V version)	HD64F2148	HD64F2148FA20	100-pin FP (FP-100B)	Under development
				HD64F2148TE20	100-pin TFP (TFP-100B)	
		Low-voltage version (3 V version)	HD64F2148V	HD64F2148VFA10	100-pin FP (FP-100B)	Under development
				HD64F2148VTE10	100-pin TFP (TFP-100B)	
	H8S/2147 Mask ROM version	Standard product (5 V version, 4 V version, 3 V version)	HD6432147	HD6432147(***)FA	100-pin FP (FP-100B)	In planning stage
				HD6432147(***)TE	100-pin TFP (TFP-100B)	
Version with on-chip I ² C bus interface (5 V version, 4 V version, 3 V version)		HD6432147W	HD6432147W(***)FA	100-pin FP (FP-100B)		
			HD6432147W(***)TE	100-pin TFP (TFP-100B)		

Table F.1 H8S/2148 Series and H8S/2144 Series Product Code Lineup (cont)
— Preliminary —

Product Type		Product Code	Mark Code	Package (Hitachi Package Code)	Notes		
H8S/2144 Series	Mask ROM version	Standard product (5 V version, 4 V version, 3 V version)	HD6432144	HD6432144(***)FA	100-pin QFP (FP-100B)	In planning stage	
				HD6432144(***)TE	100-pin TQFP (TFP-100B)		
	F-ZTAT version	Standard product (5 V/4 V version)	HD64F2144	HD64F2144FA20	100-pin QFP (FP-100B)		
				HD64F2144TE20	100-pin TQFP (TFP-100B)		
			HD64F2144V	HD64F2144VFA10	100-pin QFP (FP-100B)		Under development
				HD64F2144VTE10	100-pin TQFP (TFP-100B)		
H8S/2143	Mask ROM version	Standard product (5 V version, 4 V version, 3 V version)	HD6432143	HD6432143(***)FA	100-pin QFP (FP-100B)	In planning stage	
				HD6432143(***)TE	100-pin TQFP (TFP-100B)		
H8S/2142	Mask ROM version	Standard product (5 V version, 4 V version, 3 V version)	HD6432142	HD6432142(***)FA	100-pin QFP (FP-100B)	Under development	
				HD6432142(***)TE	100-pin TQFP (TFP-100B)		
	F-ZTAT version	Standard product (5 V/4 V version)	HD64F2142	HD64F2142FA20	100-pin QFP (FP-100B)		
				HD64F2142TE20	100-pin TQFP (TFP-100B)		
			HD64F2142V	HD64F2142VFA10	100-pin QFP (FP-100B)		Under development
				HD64F2142VTE10	100-pin TQFP (TFP-100B)		

Note: (***) is the ROM code.

The F-ZTAT version of the H8S/2148 has an on-chip I²C bus interface as standard.

The F-ZTAT 5 V/4 V version supports the operating ranges of the 5 V version and the 4 V version.

The operating range of the F-ZTAT low-voltage version will be decided later.

The above table includes products in the planning stage or under development. Information on the status of individual products can be obtained from Hitachi's sales offices.

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